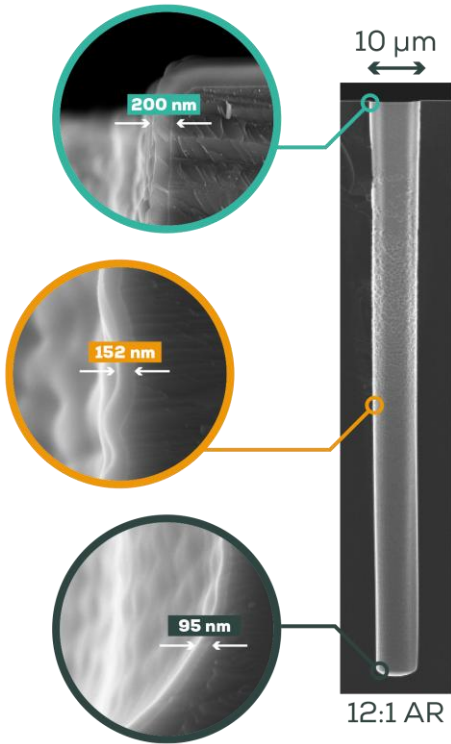


F.A.S.T.[®] for TSV

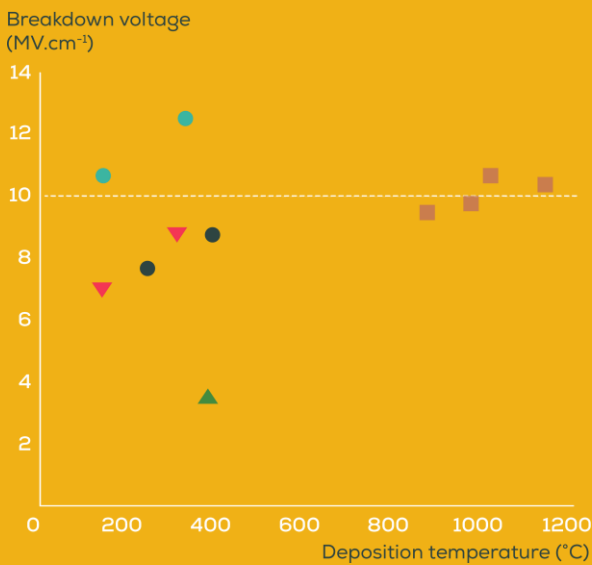
SiO₂ liner solution

F.A.S.T.
20 nm TiN / 220 nm Cu

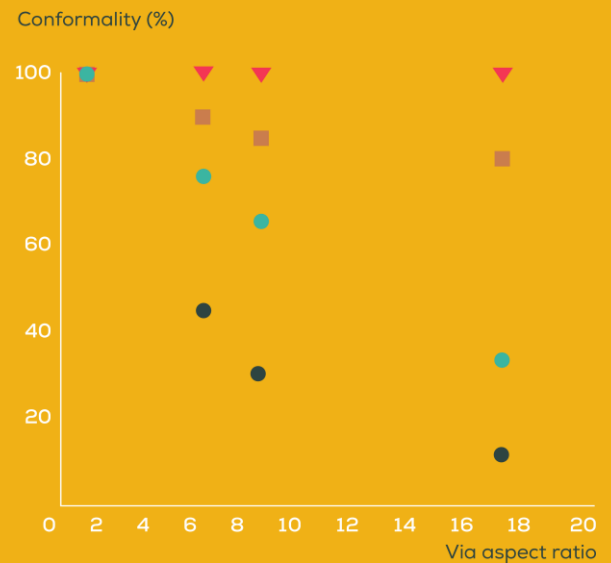


- One solution for both via middle & via last
- Conformality adjustable to integration request
- High deposition rate (> 50 nm/min)
- 200 & 300 mm single wafer cluster tools
- High throughput solution
- Low cost of ownership

ISOLATION PERFORMANCES @ LOW TEMPERATURE



BEST COMPROMISE DEPOSITION RATE/CONFORMALITY



- FAST
- PECVD
- Thermal oxide
- ▼ ALD
- ▲ SACVD

10x faster than ALD
3x higher conformality than PECVD